L Number	Hits	Search Text	DB	Time stamp
1	258157	isolation or STI	USPAT;	2004/07/14 11:48
			US-PGPUB	
2	16492	epitaxial with semiconductor	USPAT;	2004/07/14 11:55
		<u>'</u>	US-PGPUB	
3	263	(dop\$3 or implant\$3) with gas with in-situ	USPAT;	2004/07/14 12:04
			US-PGPUB	
5	0	(isolation or STI) and ((epitaxial with semiconductor) with	USPAT;	2004/07/14 11:50
		((dop\$3 or implant\$3) with gas with in-situ))	US-PGPUB	
4	3	(epitaxial with semiconductor) with ((dop\$3 or implant\$3) with	USPAT;	2004/07/14 11:53
		gas with in-situ)	US-PGPUB	
6	5	(epitaxial with semiconductor) same ((dop\$3 or implant\$3) with	USPAT;	2004/07/14 11:53
		gas with in-situ)	US-PGPUB	
7	2	(isolation or STI) and ((epitaxial with semiconductor) same	USPAT;	2004/07/14 11:53
		((dop\$3 or implant\$3) with gas with in-situ))	US-PGPUB	
8	24649	epitaxial with (semiconductor or polysiliocn or silicon)	USPAT;	2004/07/14 11:55
			US-PGPUB	
9	3	(epitaxial with semiconductor) with ((dop\$3 or implant\$3) with	USPAT;	2004/07/14 11:55
		gas with in-situ)	US-PGPUB	
11	16492	(epitaxial with semiconductor) with (epitaxial with	USPAT;	2004/07/14 11:56
		(semiconductor or polysiliocn or silicon))	US-PGPUB	0004/07/44 44:50
12	6094	(isolation or STI) and ((epitaxial with semiconductor) with	USPAT;	2004/07/14 11:56
	057070	(epitaxial with (semiconductor or polysiliocn or silicon)))	US-PGPUB	2004/07/14 11:56
13	357078	@ad>20020511 or @rlad>20020511	USPAT; US-PGPUB	2004/07/14 11.50
44	5000	((is eletion on CTI) and ((anitavial with comison dustor) with	USPAT;	2004/07/14 11:56
14	5290	((isolation or STI) and ((epitaxial with semiconductor) with (epitaxial with (semiconductor or polysiliocn or silicon)))) not	US-PGPUB	2004/07/14 11.50
		(epitaxial with (semiconductor of polyshioch of shicon)))) not [(@ad>20020511 or @rlad>20020511)	03-FGF0B	•
15	12	((dop\$3 or implant\$3) with gas with in-situ) with (epitaxial with	USPAT:	2004/07/14 11:56
15	12	((dopps of implantes) with gas with in-situ) with (epitaxial with	US-PGPUB	2004/07/14 11:50
16	11	(((dop\$3 or implant\$3) with gas with in-situ) with (epitaxial with	USPAT;	2004/07/14 11:56
10		((dopps of implantes) with gas with in-site) with (epitexial with (semiconductor or polysiliocn or silicon))) not (@ad>20020511	US-PGPUB	2001/01/11 11:00
		or @rlad>20020511)	55.5.55	
17	5	(isolation or STI) and ((((dop\$3 or implant\$3) with gas with	USPAT;	2004/07/14 11:57
1		in-situ) with (epitaxial with (semiconductor or polysiliocn or	US-PGPUB	
		silicon))) not (@ad>20020511 or @rlad>20020511))		
18	2859	(dop\$3 or implant\$3) with in-situ	USPAT;	2004/07/14 12:04
		(22,772.0	US-PGPUB	
19	111	(epitaxial with (semiconductor or polysiliocn or silicon)) with	USPAT;	2004/07/14 12:04
		((dop\$3 or implant\$3) with in-situ)	US-PGPUB	
20	58	(isolation or STI) and ((epitaxial with (semiconductor or	USPAT;	2004/07/14 12:05
		polysiliocn or silicon)) with ((dop\$3 or implant\$3) with in-situ))	US-PGPUB	
21	48	((isolation or STI) and ((epitaxial with (semiconductor or	USPAT;	2004/07/14 12:05
		polysiliocn or silicon)) with ((dop\$3 or implant\$3) with in-situ)))	US-PGPUB	
		not (@ad>20020511 or @rlad>20020511)		